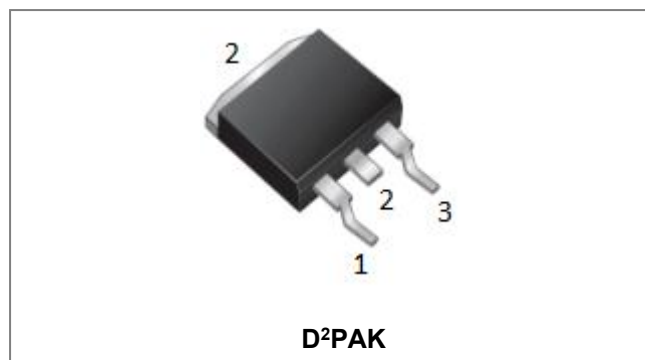


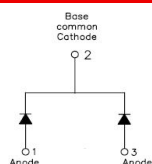
STB4080C SCHOTTKY RECTIFIER



Features

- 150°C T_J operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	80	V
Average Rectified Forward Current (Per Device)	I _{F (AV)}	50% duty cycle @T _c =105°C, rectangular wave form	20(Per Leg) 40(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	300	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg) *	V _{F1}	@ 5A, Pulse, T _J = 25 °C	0.45	-	V
		@ 10A, Pulse, T _J = 25 °C	0.54	-	
		@ 20A, Pulse, T _J = 25 °C	0.69	0.75	
	V _{F2}	@ 5A, Pulse, T _J = 125 °C	0.40	-	V
		@ 10A, Pulse, T _J = 125 °C	0.52	-	
		@ 20A, Pulse, T _J = 125 °C	0.65	0.70	
Reverse Current (Per Leg) *	I _{R1}	@V _R = rated V _R , T _J = 25°C	0.02	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125°C	14	75	mA
Junction Capacitance(Per Leg)	C _T	@V _R = 5V, T _C = 25 °C, f _{SIG} = 1MHz	811	-	pF

* Pulse width < 300 μs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	°C
Storage Temperature	T_{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	$R_{\theta JC}$	DC operation	2	°C/W
Approximate Weight	wt	-	1.85	g
Case Style	D ² PAK			

Ratings and Characteristics Curves

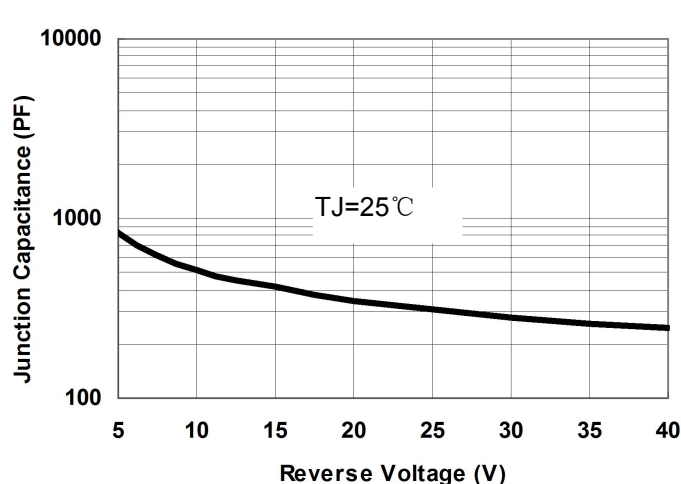


Fig.1-Typical Junction Capacitance

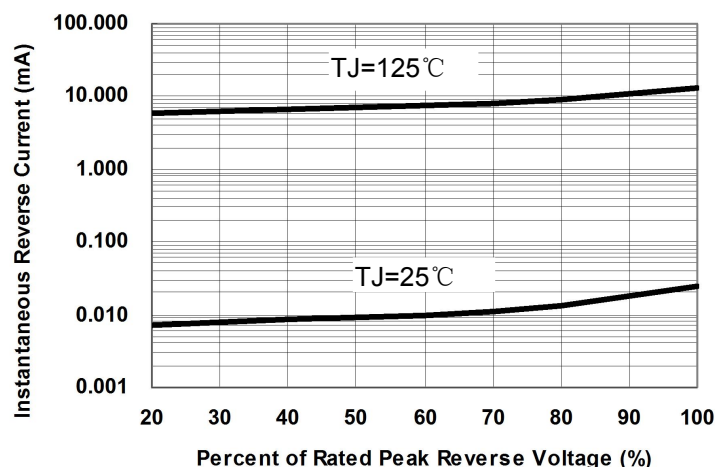


Fig.2-Typical Reverse Characteristics

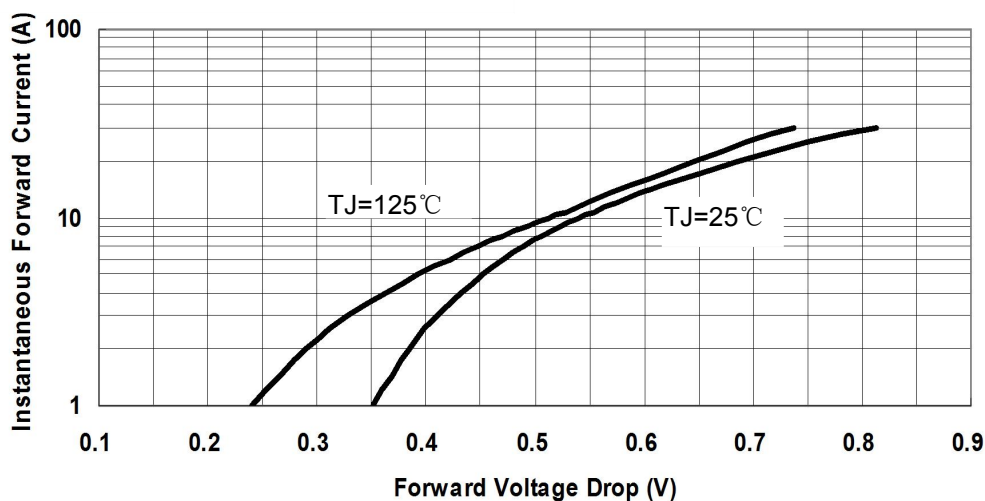
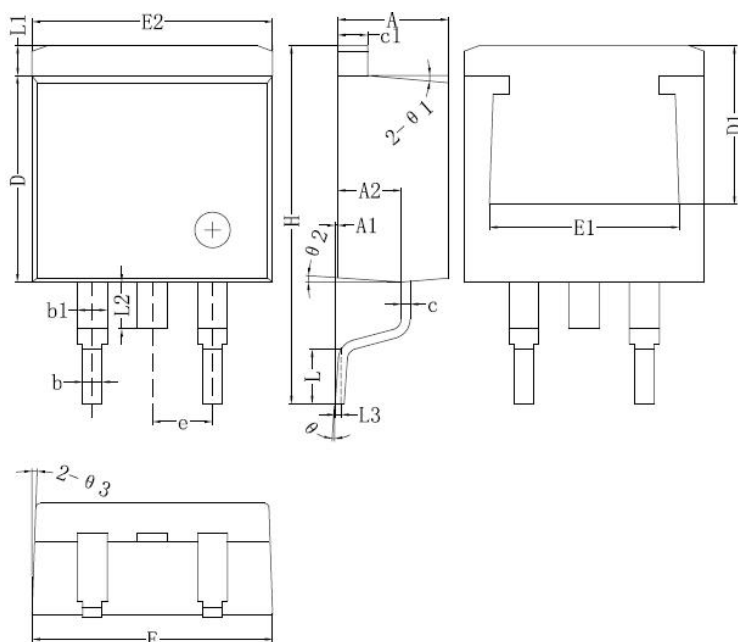


Fig.3-Typical Instantaneous Forward Voltage Characteristics

Mechanical Dimensions D²PAK



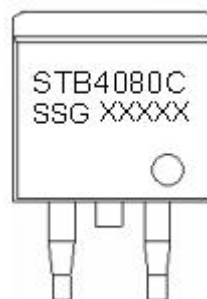
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
c	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
e		2.54	
H	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
e	0	-	8°
e1		5°	
e2		4°	
e3		4°	

Ordering Information

Device	Package	Shipping
STB4080C	D ² PAK	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

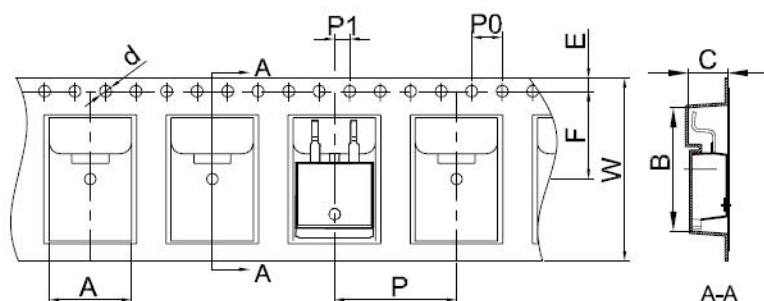


Where XXXXX is YYWWL

ST = Device Type
B = Package type
40 = Forward Current (40A)
80 = Reverse Voltage(80V)
C = Configuration
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification D²PAK



SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

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